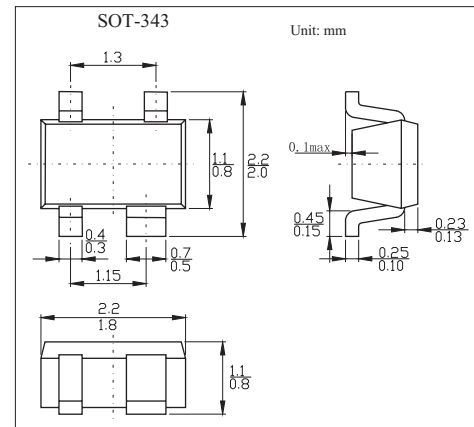


■ Features

- Low barrier diode for detectors up to GHz frequencies.



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	40	V
Forward current	I_F	20	mA
Total power dissipation, $T_s = 103^\circ\text{C}$	P_{tot}	100	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to + 150	$^\circ\text{C}$
Junction - ambient	$R_{th JA}$	≤ 630	K/W
Junction - soldering point	$R_{th JS}$	≤ 470	K/W

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse current	I_R	$V_R = 40\text{ V}$			10	μA
Forward voltage	V_F	$I_F = 2\text{ mA}$		0.58	1	V
Diode capacitance	C_T	$f = 1\text{ MHz}; V_R = 0$		0.35	0.6	pF
Case capacitance	C_C	$f = 1\text{ MHz}$		0.1		pF
Differential resistance	R_O	$V_R = 0, f = 10\text{ KHz}$		225		K Ω
Series inductance chip to ground	L_s			2		nH

■ Marking

Marking	62s
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